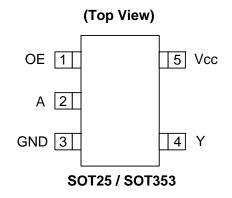


SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Description

The 74AHCT1G126 is a single non-inverting buffer/bus driver with a 3-state output. The output enters a high impedance state when a LOW-level is applied to the output enable (OE) pin. The device is designed for operation with a power supply range of 4.5V to 5.5V.

Pin Assignments



Features

- Supply Voltage Range from 4.5V to 5.5V
- ± 8 mA Output Drive at 5.0V
- CMOS low power consumption
- Schmitt Trigger Action at All Inputs Make the Circuit Tolerant for Slower Input Rise and Fall Time.
- ESD Protection per JESD 22
 - Exceeds 200-V Machine Model (A115-A)
 - Exceeds 2000-V Human Body Model (A114-A)
 - Exceeds 1000-V Charged Device Model (C101C)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- SOT25 and SOT353: Assembled with "Green" Molding Compound (no Br, Sb)
- Lead Free Finish / RoHS Compliant (Note 1)

Applications

- General Purpose Logic
- Wide array of products such as:
 - o PCs, networking, notebooks, netbooks, PDAs
 - o Computer peripherals, hard drives, CD/DVD ROM
 - \circ $\;$ TV, DVD, DVR, set top box
 - o Phones, Personal Navigation / GPS
 - o MP3 players ,Cameras, Video Recorders

Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at http://www.diodes.com/products/lead_free.html.

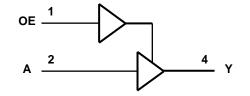


SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Pin Descriptions

Pin Name	Pin No.	Description
OE	1	Output Enable
A	2	Data Input
GND	3	Ground
Y	4	Data Output
V _{CC}	5	Supply Voltage

Logic Diagram



Function Table

Inp	Output	
OE	Α	Y
Н	Н	Н
Н	L	L
L	Х	Z



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Absolute Maximum Ratings (Note 2)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD CDM	Charged Device Model ESD Protection	1	KV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current V _I <0	-20	mA
Ι _{ΟΚ}	Output Clamp Current ($V_O < 0$ or $V_O > V_{CC}$)	±20	mA
Ι _Ο	Continuous output current ($V_O = 0$ to V_{CC})	±25	mA
I _{CC}	Continuous current through V _{CC}	50	mA
I _{GND}	Continuous current through GND	-50	mA
T _J Operating Junction Temperature		-40 to 150	°C
T _{STG}	Storage Temperature	-65 to 150	°C

Notes: 2. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

Recommended Operating Conditions (Note 3)

Symbol		Parameter	Min	Max	Unit
V _{CC}	Operating Voltage		4.5	5.5	V
VIH	High-level Input Voltage		2.0		V
V _{IL}	Low-level input voltage			0.8	V
VI	Input Voltage		0	5.5	V
Vo	Output Voltage		0	V _{CC}	V
I _{OH}	High-level output current			-8	mA
I _{OL}	Low-level output current			8	mA
Δt/ΔV	Input transition rise or fall rate			20	ns/V
T _A	Operating free-air temperature		-40	125	°C

Notes: 3. Unused inputs should be held at V_{CC} or Ground.



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Electrical Characteristics

		Terrore			25⁰C		-40ºC t	o 85⁰C	-40°C to	o 125⁰C	
Symbol	Parameter	Test Conditions	V _{CC}	Min	Тур.	Max	Min	Max	Min	Max	Unit
	High Level	I _{OH} = -50μA	4.5V	4.4	4.5		4.4		4.4		
V _{OH}	Output Voltage	I _{OH} = -8mA	4.5V	3.94			3.8		3.70		V
V	Low Level	I _{OL} = 50μA	4.5V		0	0.1		0.1		0.1	V
V _{OL}	Output Voltage	I _{OL} = 8mA	4.5V			0.36		0.44		0.55	v
l _l	Input Current	$V_I = 5.5V \text{ or } GND$	0 to 5.5V			± 0.1		± 1		±2	μA
I _{OZ}	Z State Leakage Current	V _O =0 to 5.5V	5.5V			0.25		2.5		10	μΑ
I _{CC}	Supply Current	$V_{I} = 5.5V \text{ or GND}$ $I_{O}=0$	5.5V			1		10		40	μA
Ci	Input Capacitance	V _I = V _{CC} – or GND	5.5V		2.0	10		10		10	pF
ΔI _{CC}	Additional Supply Current	One input at 3.4 V Other inputs at V _{CC} or GND	5.5V			1.35		1.5			mA
0	Thermal Resistance	SOT25			204						0000
θ_{JA}	Junction-to- Ambient	SOT353	(Note 4)		371						°C/W
	Thermal Resistance	SOT25			52						°0.00
θ _{JC}	Junction-to- Case	SOT353	(Note 4)		143						°C/W

Note: 4. Test conditions for SOT25, and SOT353: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Switching Characteristics

$V_{CC} = 5V \pm 0.5V$ (see Figure 1)

Parameter	From	то			25⁰C		-40ºC t	o 85ºC	-40ºC to	o 125⁰C	Unit
Farameter	(Input)	(OUTPUT)		Min	Тур.	Max	Min	Max	Min	Max	Unit
	٨	V	C _L =15pF	0.6	3.4	5.5	0.6	6.5	0.6	7.0	ns
t _{pd}	A	Ť	C _L =50pF	0.6	4.7	7.5	0.6	8.5	0.6	9.5	ns
+	OE	V	C _L =15pF	0.6	3.6	5.6	0.6	6.3	0.6	6.5	ns
t _{en}	UE	ř	C _L =50pF	0.6	5.4	8.0	0.6	9.0	0.6	9.0	ns
		V	C _L =15pF	0.6	4.3	6.8	0.6	8.0	0.6	8.5	ns
t _{dis}	OE	ř	C _L =50pF	0.6	6.1	8.8	0.6	10.0	0.6	11.0	ns

Operating Characteristics

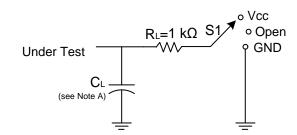
 $T_A = 25 \ ^{o}C$

	Parameter	Test Conditions	V _{CC} = 5 V Typ.	Unit
C _{pd}	Power dissipation capacitance	f = 1 MHz No Load	11	pF



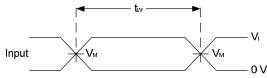
SINGLE BUFFER GATE WITH 3-STATE OUTPUT

Parameter Measurement Information

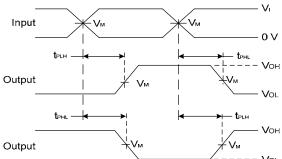


TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	Vload
t _{PHZ} /t _{PZH}	GND

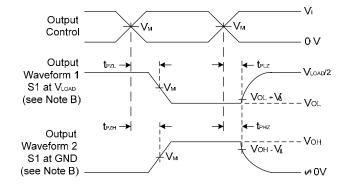
Maa	In	puts	V	•	MA
Vcc	VI	t _r /t _f	V _M	CL	VΔ
5V±0.5V	V _{CC}	≤3ns	V _{CC} /2	15pF	0.3V
5V±0.5V	V _{CC}	≤3ns	V _{CC} /2	50pF	0.3V



Voltage Waveform Pulse Duration







Voltage Waveform Enable and Disable Times Low and High Level Enabling

Figure 1. Load Circuit and Voltage Waveforms

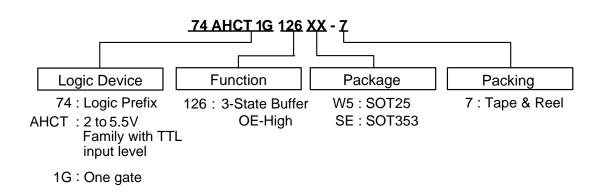
Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate \leq 1 MHz.
- C. Inputs are measured separately one transition per measurement.
- D. t_{PLZ} and t_{PHZ} are the same as $t_{dis.}$
- E. tPZL and tPZH are the same as tEN
- F. tPLH and tPHL are the same as tPD.



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

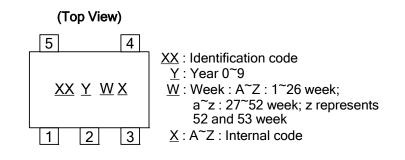
Ordering Information



	Device Package Packaging		7" Tape and Reel		
	Device	Code	(Note 5)	Quantity	Part Number Suffix
B	74AHCT1G126W5-7	W5	SOT25	3000/Tape & Reel	-7
B	74AHCT1G126SE-7	SE	SOT353	3000/Tape & Reel	-7

Notes: 5. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

Marking Information



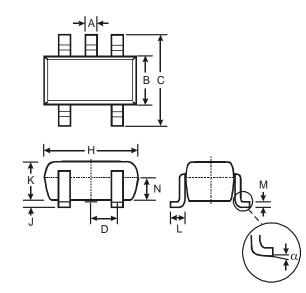
Part Number	Package	Identification Code	
74AHCT1G126W5	SOT25	ZZ	
74AHCT1G126SE	SOT353	ZZ	



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

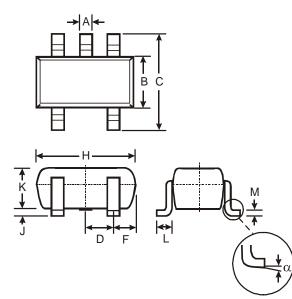
Package Outline Dimensions (All Dimensions in mm)

(1) Package Type: SOT25



SOT25							
Dim	Min	Max	Тур				
Α	0.35	0.50	0.38				
В	1.50	1.70	1.60				
С	2.70	3.00	2.80				
D	_	_	0.95				
Н	2.90	3.10	3.00				
J	0.013	0.10	0.05				
Κ	1.00	1.30	1.10				
L	0.35	0.55	0.40				
М	0.10	0.20	0.15				
Ν	0.70	0.80	0.75				
α	0°	8°					
All D	All Dimensions in mm						

(2) Package Type: SOT353



SOT353		
Dim	Min	Max
Α	0.10	0.30
В	1.15	1.35
С	2.00	2.20
D	0.65 Typ	
F	0.40	0.45
Н	1.80	2.20
J	0	0.10
κ	0.90	1.00
L	0.25	0.40
М	0.10	0.22
α	0°	8°
All Dimensions in mm		



SINGLE BUFFER GATE WITH 3-STATE OUTPUT

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